

Books

1. Stephen E. Saddow and **Anant Agarwal**, "Advances in Silicon Carbide Processing and Applications," Artech House, 2004.

Book Chapters

1. S. Sriram, R. R. Siergiej, R. C. Clarke, **A. K. Agarwal**, and C. D. Brandt, "SiC for Microwave Power Transistors," *Silicon Carbide - A Review of Fundamental Questions and Applications to Current Device Technology*, Volume II, edited by Wolfgang J. Choyke, Hiroyuki Matsunami, and Gerhard Pensl, Akademie Verlag GmbH, Berlin 1997.
2. C. D. Brandt, R. C. Clarke, R. R. Siergiej, J. B. Casady, S. Sriram, and **A. K. Agarwal**, "Chapter-5, SiC for Applications in High-Power Electronics," *Semiconductors and Semimetals*, Academic Press, Vol 52, 1998.
3. **A. K. Agarwal**, S.-H. Ryu, and J. Palmour, "Power MOSFETs in 4H-SiC: Device Design and Technology," in *Silicon Carbide, Recent Major Advances*, edited by W. J. Choyke, H. Matsumani, and G. Pensl, Springer-Verlag, Berlin Heidelberg 2004, Germany, pp. 785 – 812.
4. **A. K. Agarwal**, S.-H. Ryu, and J. Palmour, "Power and RF BJTs in 4H-SiC – Device Design and Technology," in *Silicon Carbide Processing and Applications*, edited by S Sadow and A. Agarwal, to be published by Artech house, Inc., of Norwood, MA, USA.
5. M. E. Levinshtein, S. L. Rumyantsev, T. T. Mnatsakanov, **Anant K. Agarwal** and John W. Palmour "SiC thyristors" in: "SiC Materials and Devices – vol. 1", ed. by M. S. Shur, S. L. Rumyantsev and M. E. Levisnhtein, World Sci. (2006), ISBN 981-256-835-2.
6. Aivars J. Lelis, Robert E. Stahlbush, Ronald Green, Daniel B. Habersat, Charles Cheung, Minseok Kang, **Anant Agarwal**, Akin Akturk, James M. McGarrity, "Reliability of SiC MOSFETs", 2019 (to be published in 2020).
7. Arash Salemi, Minseok Kang, Woongje Sung, **Anant K. Agarwal**, "Device Processing Chain and Processing SiC in a Foundry Environment" to be published in 2020 by Wiley.